Diode Semiconductor Device - Page 1 of 1



Inc	losure Material:
Gla	ss and metal
Ove	erall Length:
0.4	50 inches
Ove	erall Diameter:
0.6	67 inches
Мо	unting Facility Quantity:
1	
Мо	unting Method:
Thr	eaded stud
Fea	atures Provided:
Her	metically sealed case
Ove	erall Width Across Flats:
0.6	87 inches
Thr	ead Size:
0.2	50 inches
Ser	niconductor Material:
Sili	con
Vol	tage Rating In Volts Per Characteristic:
50.	0 regulator voltage
Cu	rrent Rating Per Characteristic:
250	0.00 milliamperes repetitive peak forward current
Ρο	wer Rating Per Characteristic:
50.	0 watts small-signal input power, common-collector preset
Ma	ximum Operating Tempurature Per Measurement Point:
175	i.0 degrees celsius junction
Thr	ead Series Designator:
Unf	
Ter	minal Type And Quantity:
1 ta	b, solder lug and 1 threaded stud
Spe	ecification Data:
801	31-release3669 professional/industrial association specification
She	elf Life:
N/a	
Uni	t Of Measure:
Dei	nilitarization:
No	
Fiig	J: